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Title: Density Functional Theory Calculations of Mass Transport in UO<sub>2</sub>

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## Density functional theory calculations of mass transport in $\text{UO}_2$

In this talk we present results of density functional theory (DFT) calculations of U, O and fission gas diffusion in  $\text{UO}_2$ . These processes all impact nuclear fuel performance. For example, the formation and retention of fission gas bubbles induce fuel swelling, which leads to mechanical interaction with the clad thereby increasing the probability for clad breach. Alternatively, fission gas can be released from the fuel to the plenum, which increases the pressure on the clad walls and decreases the gap thermal conductivity. The evolution of fuel microstructure features is strongly coupled to diffusion of U vacancies. Since both U and fission gas transport rates vary strongly with the O stoichiometry, it is also important to understand O diffusion.

In order to better understand bulk Xe behavior in  $\text{UO}_{2+x}$  we first calculate the relevant activation energies using DFT techniques. By analyzing a combination of Xe solution thermodynamics, migration barriers and the interaction of dissolved Xe atoms with U, we demonstrate that Xe diffusion predominantly occurs via a vacancy-mediated mechanism. Since Xe transport is closely related to diffusion of U vacancies, we have also studied the activation energy for this process. In order to explain the low value of 2.4 eV found for U migration from independent damage experiments (not thermal equilibrium) the presence of vacancy clusters must be included in the analysis.

Next we investigate species transport on the (111)  $\text{UO}_2$  surface, which is motivated by the formation of small voids partially filled with fission gas atoms (bubbles) in  $\text{UO}_2$  under irradiation. Surface diffusion could be the rate-limiting step for diffusion of such bubbles, which is an alternative mechanism for mass transport in these materials. As expected, the activation energy for surface diffusion is significantly lower than for bulk transport. These results are further discussed in terms of engineering-scale fission gas release models.

Finally, oxidation of  $\text{UO}_2$  and the importance of cluster formation for understanding thermodynamic and kinetic properties of  $\text{UO}_{2+x}$  are investigated.

# Density Functional Theory Calculations of Mass Transport in $\text{UO}_2$

**David Andersson<sup>1</sup>, Boris Dorado<sup>2</sup>, Blas Uberuaga<sup>1</sup>  
and Chris Stanek<sup>1</sup>**

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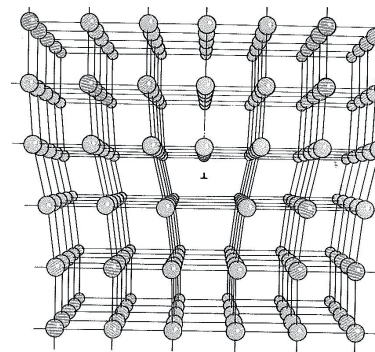
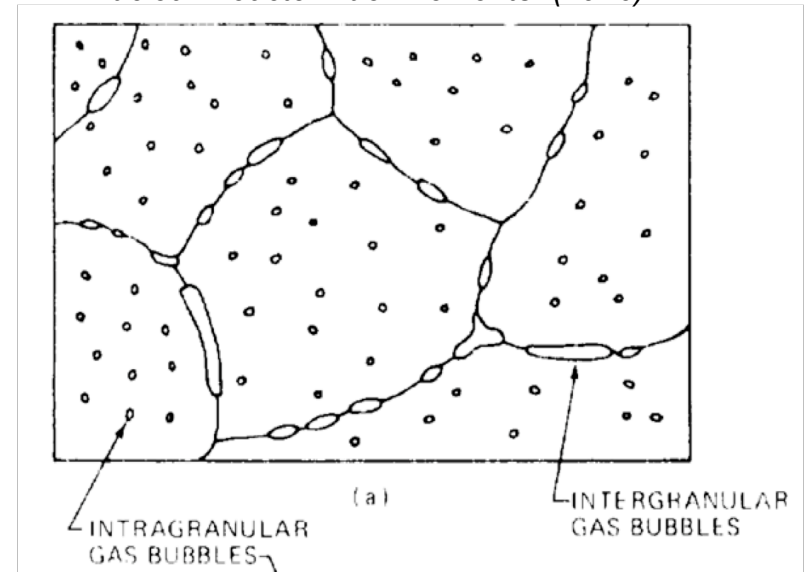
**<sup>2</sup>CEA, DEN, DEC, Centre de Cadarache, France**

**Funding acknowledgement:** DOE Nuclear Energy Fuel Cycle Research and Development (FCRD) Campaign, Nuclear Energy Advanced Modeling and Simulation (NEAMS) Program.

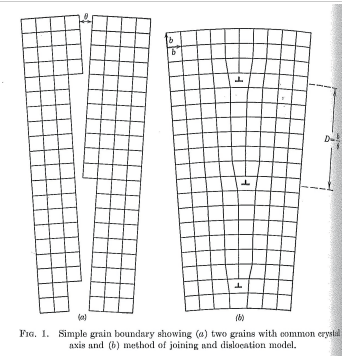
## Motivation and Objectives

- Formation, redistribution and release of FG are critical determinants of nuclear fuel performance.
- The first controlling step for FG release is diffusion of individual gas atoms to existing gas bubbles or grain boundaries (sinks) governed by the activation energy for bulk diffusion.
- For predictive capabilities need to establish underlying atomistic mechanisms and determine model parameters.
- The next step in the fission gas release process is interactions with microstructure features.

*D.R. Olander, "Fundamental Aspects of Nuclear Reactor Fuel Elements" (1976)*

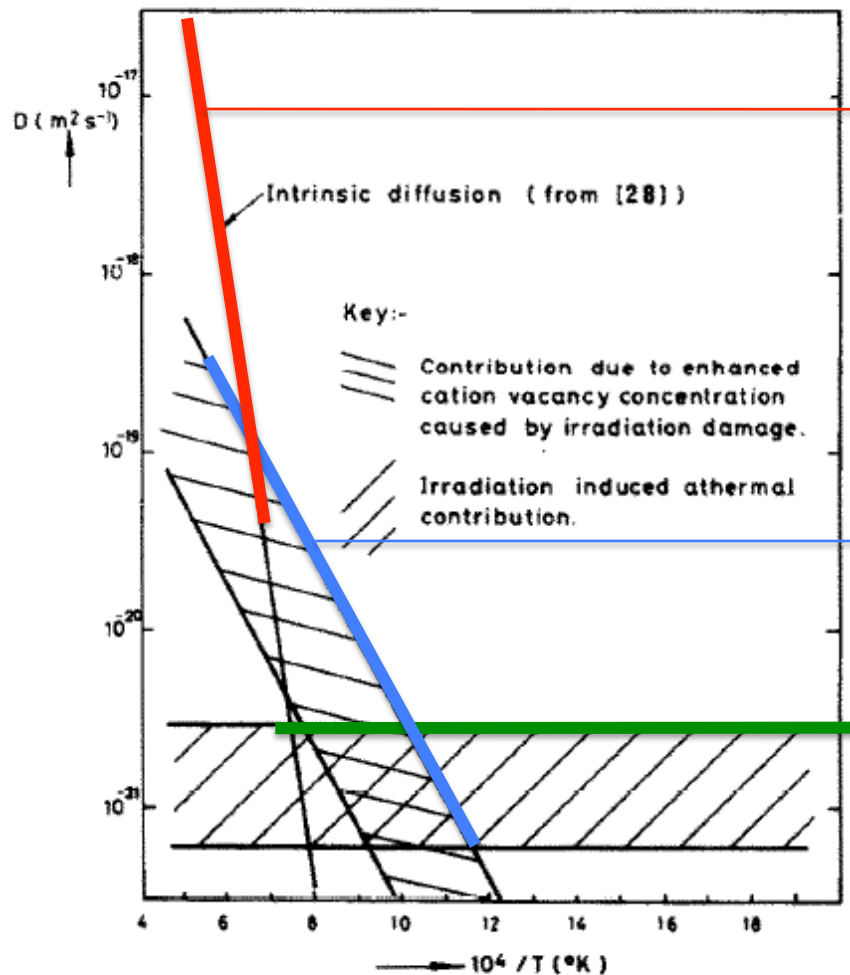


From C.A. Wert and R.M. Thomson "Physics of Solids" (1964).



From W.T. Read Jr. and W. Shockley, in F. Seitz "Imperfections in Nearly Perfect Crystals" (1952).

# Atomistic Simulations to Reveal Fission Gas Diffusion Mechanistics



$$\text{Thermal diffusion } D = 7.6 \cdot 10^{-10} \exp\left(-\frac{3.04}{k_B T}\right)$$

Calculations for the same conditions yield 3.94 eV, in good agreement with more recent measurements of intrinsic diffusion (3.9 eV).

$$\text{Enhanced diffusion } D = C \times \sqrt{\dot{F}} \exp\left(-\frac{1.20}{k_B T}\right)$$

Enhanced vacancy concentration due to irradiation. Improved data for unit processes yields 3.17 eV. Better agreement with FG bubble transport controlled by surface diffusion (1.00-1.25 eV).

Fig. 10. Possible components of the in-pile rare gas diffusion coefficient.

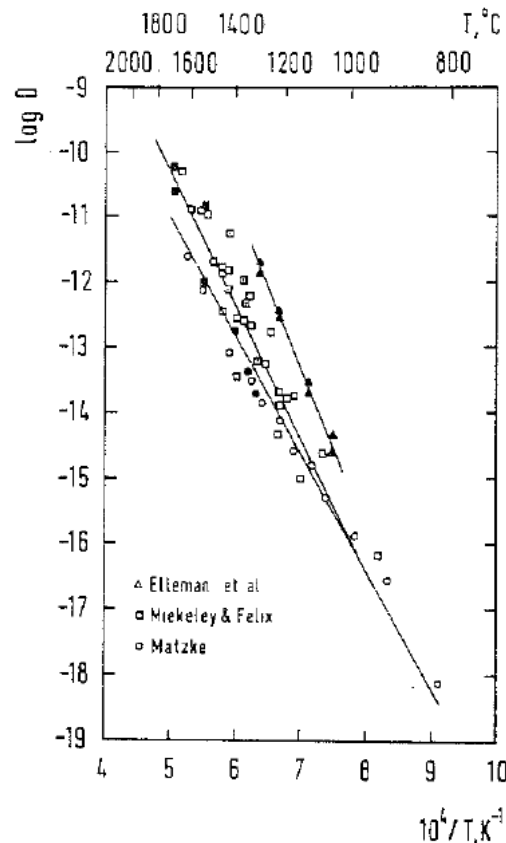
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Turnbull et al., J. Nucl. Mater. 107, 168 (1982).

Model was derived for stoichiometric  $\text{UO}_2$ , currently limited consideration of changes in stoichiometry, composition, etc.

# Experimental Activation Energies for U and Xe Diffusion in $\text{UO}_{2\pm x}$

Experiments, e.g. Hj. Matzke, *Radiation Effects* **53** (1980) 219.



$\Delta H_A$  Xe:

$$\Delta H_A = 6.0 \text{ eV } \text{UO}_{2-x}$$

$$\Delta H_A = 3.9 \text{ eV } \text{UO}_2$$

$$\Delta H_A = 1.7 \text{ eV } \text{UO}_{2+x}$$

$\Delta H_A$  U:

$$\Delta H_A = 7.8 \text{ eV } \text{UO}_{2-x}$$

$$\Delta H_A = 5.6 \text{ eV } \text{UO}_2$$

$$\Delta H_A = 2.6 \text{ eV } \text{UO}_{2+x}$$

Easier to form U  
vacancy for  $x > 0$  and  
 $x = 0$  than for  $x < 0$ .

- Effective activation energies determined decades ago, but mechanistic aspects not well understood.

$$D = D_0 \exp\left(-\frac{\Delta H_A}{k_B T}\right)$$

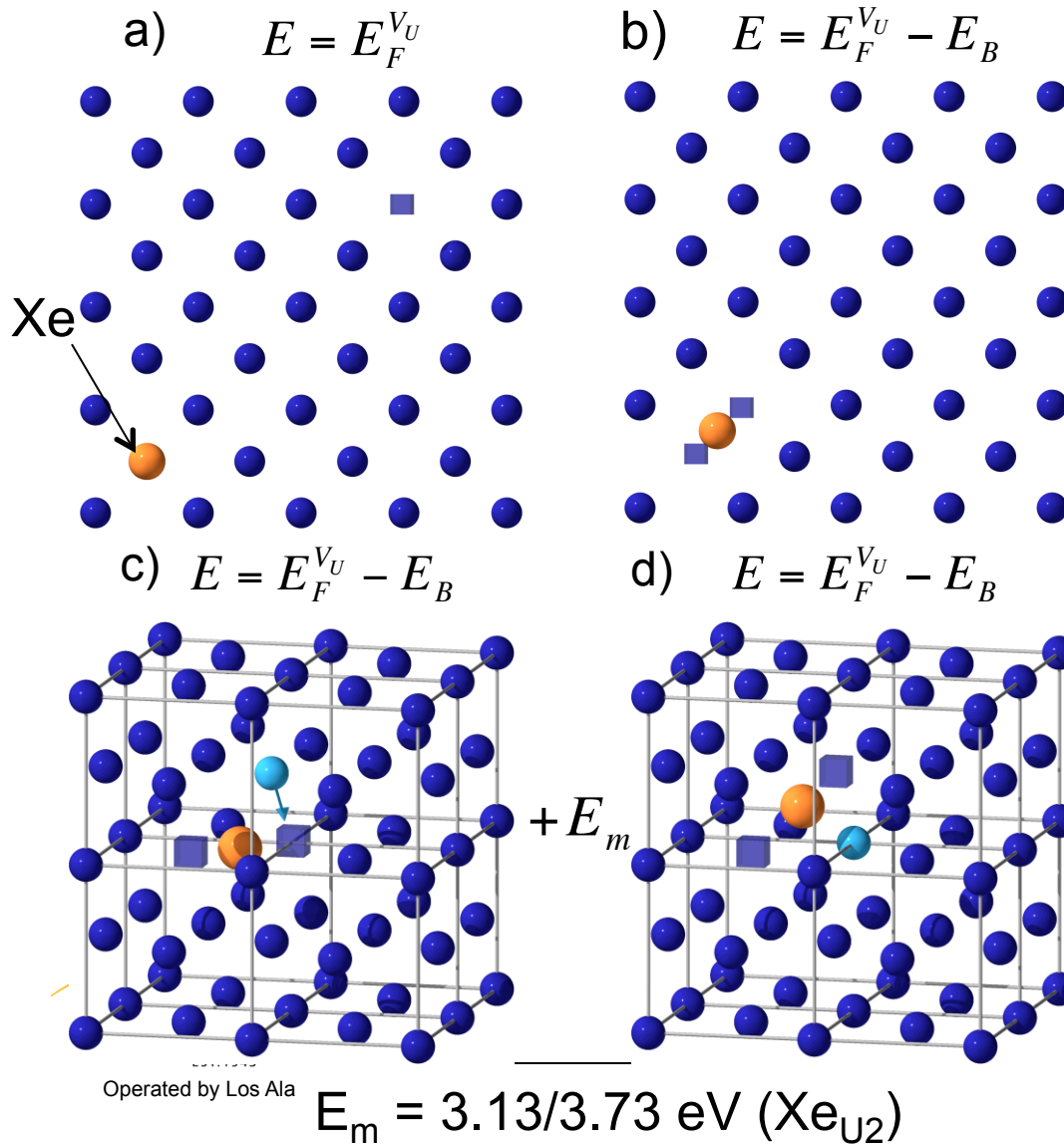
- Required for formulating accurate and predictive diffusion models that account for irradiation.

## Methodology

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- Density functional theory calculations using VASP.
- Lichtenstein LDA+ $U$  for U 5f electrons. Literature values for  $U$  ( $U=4.5$  and  $J=0.51$  eV). AFM magnetic order is prescribed in all simulations.
- Electronic ground-state determined by occupation matrix control (Dorado *et al.*, PRB 82 035114 (2010), PRB 79 235125 (2009)), reduced symmetries, structural distortions and other methods (e.g., Meredig *et al.* PRB 82 195128 (2010) and Geng *et al.* Phys. Rev. B 82, 094106 (2010)).
- $2\times 2\times 2$  and  $2\times 2\times 3$  fluorite supercell. Ionic relaxations, volume kept fixed.
- MD to find minimum energy structures for complex defects.
- Nudged elastic band (NEB) technique for calculation of migration barriers.
- Charged supercells to model mixed valence character.
- For details see Andersson *et al.*, PRB 84 054105 (2011).

# First Principles Calculations of Bulk Xe Diffusion

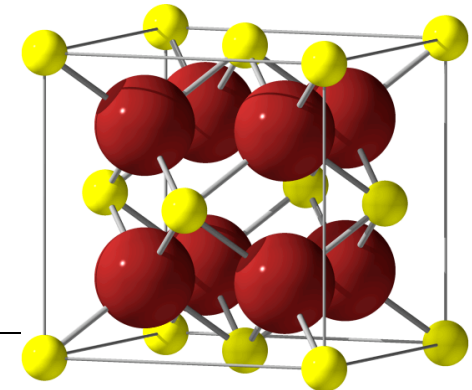


$$\Delta E_a^{Xe} = E_{VU}^F - E_B + E_m^{VU,C}(T)$$

Xe atoms occupy different trap sites as function of the  $\text{UO}_{2\pm x}$  stoichiometry.

|                        | $E_m^{VU,C} \text{ (eV)}$ |
|------------------------|---------------------------|
| $\text{Xe}_{U_2}$      | 3.77                      |
| $\text{Xe}_{U_{2O}}$   | 5.28                      |
| $\text{Xe}_{U_{2O_2}}$ | 5.13                      |

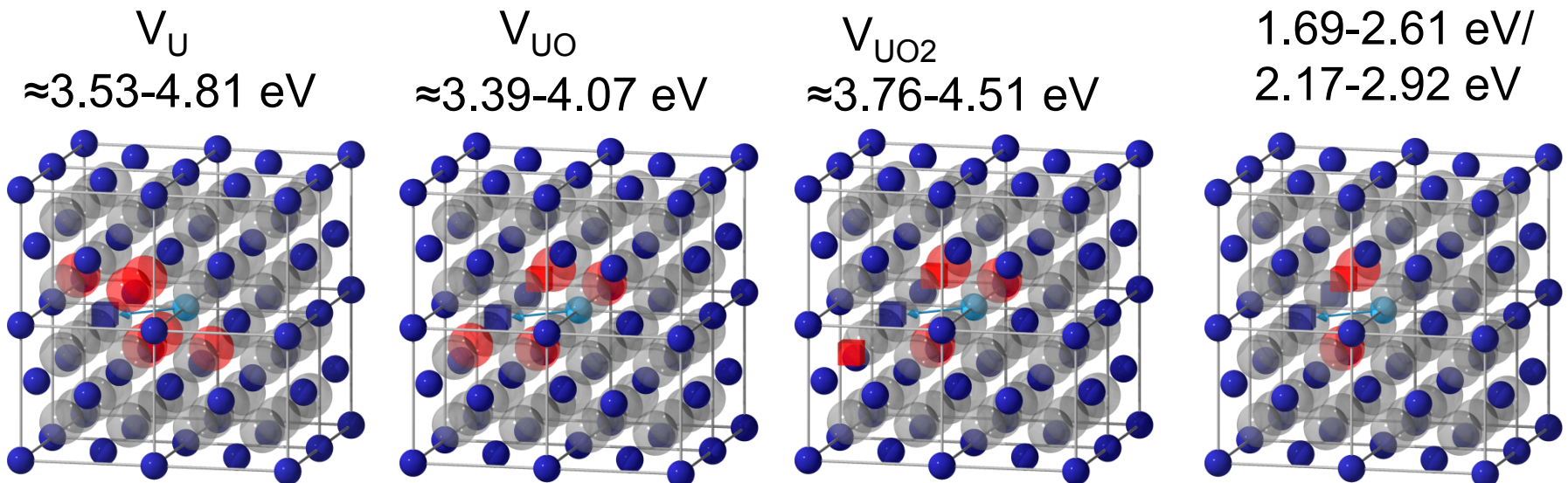
Fluorite structure:





## Bulk U Diffusion Mechanism from DFT

$$\Delta E_a^U = E_{VUOx}^F + E_m^{VUOx}(T)$$



- High barrier is for  $a_0=5.45$  (LDA+ $U$ ) and low barrier for  $a_0=5.525$  (GGA+ $U$ ), possibly related to thermal expansion but current assessment put higher confidence in the LDA+ $U$  barrier.
- Significant displacement of neighboring O ions for  $V_U$ ,  $V_{UO}$  and  $V_{UO_2}$ .
- $V_U$  different from exp. barrier (2.4 eV). Explained by  $V_{U_2O}$  or  $V_{U_2}$  clustering. Experimental barrier obtained for damaged materials.

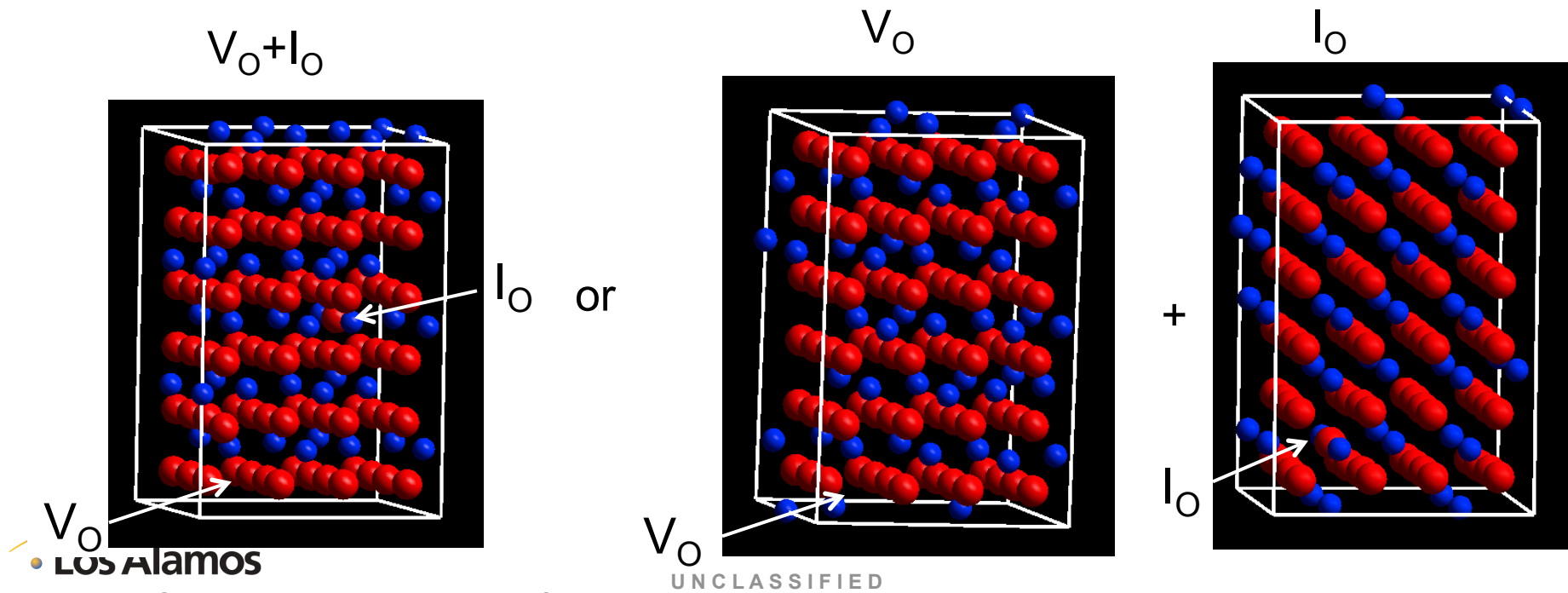
# Calculating the Defect Parameters; Charge Compensation

Simplified thermodynamic defect model due to Catlow<sup>1</sup>

$$E_a^{Xe} = E_{VU}^F - E_B + E_m^{VU,C}(T)$$

Oxygen Frenkel pair as an example:

|            | UO <sub>2-x</sub>    | UO <sub>2</sub>                       | UO <sub>2+x</sub>          |
|------------|----------------------|---------------------------------------|----------------------------|
| $V_U$      | $E_t = E_S$          | $E_t = E_S - E_F$                     | $E_t = E_S - 2E_F$         |
| $V_{UO}$   | $E_t = E_S - B_{dv}$ | $E_t = E_S - \frac{1}{2}E_F - B_{dv}$ | $E_t = E_S - E_F - B_{dv}$ |
| $V_{UO_2}$ | $E_t = E_S - B_{nt}$ | $E_t = E_S - B_{nt}$                  | $E_t = E_S - B_{nt}$       |



Listen to Crocombette (next talk) for extensive work on this topic.

# First Principles Calculations of Defect Formation Energies

Simplified thermodynamic defect model due to Catlow<sup>1</sup>

|                             | UO <sub>2-x</sub>    | UO <sub>2</sub>                       | UO <sub>2+x</sub>          |
|-----------------------------|----------------------|---------------------------------------|----------------------------|
| V <sub>U</sub>              | $E_t = E_S$          | $E_t = E_S - E_F$                     | $E_t = E_S - 2E_F$         |
| V <sub>UO</sub>             | $E_t = E_S - B_{dv}$ | $E_t = E_S - \frac{1}{2}E_F - B_{dv}$ | $E_t = E_S - E_F - B_{dv}$ |
| V <sub>UO<sub>2</sub></sub> | $E_t = E_S - B_{nt}$ | $E_t = E_S - B_{nt}$                  | $E_t = E_S - B_{nt}$       |

$$\Delta E_a^{Xe} = E_{VU}^F - E_B + E_m^{VU,C}(T)$$

$$\Delta E_a^U = E_{VUOx}^F + E_m^{VUOx}(T)$$

|                         | E <sub>F</sub> (eV) | E <sub>S</sub> (eV) | B <sub>dv</sub> (eV) | B <sub>nt</sub> (eV) |
|-------------------------|---------------------|---------------------|----------------------|----------------------|
| Neutral                 | 5.26/6.40           | 10.15/11.96         | 2.93/3.35            | 5.58/6.46            |
| Charged                 | 3.32/4.26           | 6.00/7.65           | 1.22/1.52            | 1.43/3.15            |
| One supercell           | 3.39/4.10           | 6.39/7.12           | 1.20/1.33            | 1.82/1.62            |
| Ref. Exp <sup>1,2</sup> | 3.0-4.0             | 6-7                 | --                   | --                   |

“Fluorite”/”J-T”

- Charged supercell calculations include corrections for Coulomb interactions and potential alignments.



Charged or One supercell give best agreement with experiments.

<sup>1</sup>C. R. A. Catlow, Radiat. Eff. Defect. S. 53, 127 (1980).

<sup>2</sup> Hj. Matzke, in Diffusion Processes in Nuclear Materials, ed. R. P. Agarwala, North-Holland, Amsterdam, 1992.



# Comparison of First Principles Results to Experimental Values

$$\Delta E_a^{Xe} = E_{VU}^F - E_B + E_m^{VU,C}(T)$$

$$\Delta E_a^U = E_{VUOx}^F + E_m^{VUOx}(T)$$

|                             | Calc.     | Exp[1] |
|-----------------------------|-----------|--------|
| $\Delta E_a^U(VO_{2-x})$    | 7.94-8.69 | 7.8    |
| $\Delta E_a^U(VO_2)$        | 6.52-7.20 | 5.6    |
| $\Delta E_a^U(VO_{2+x})$    | 2.90-4.18 | 2.6    |
| $\Delta E_a^{Xe}(VO_{2-x})$ | 6.52-7.12 | 6.0    |
| $\Delta E_a^{Xe}(VO_2)$     | 4.39-4.99 | 3.9    |
| $\Delta E_a^{Xe}(VO_{2+x})$ | 1.47-2.07 | 1.7    |

|                    | Calc.            | Exp. [1] |
|--------------------|------------------|----------|
| $E_B(Xe_{VO_2})$   | 2.69 (2.32-3.49) | --       |
| $E_B(Xe_{VO})$     | 1.43 (1.30-1.95) | --       |
| $E_B(Xe_V)$        | 1.02 (0.36-1.48) | --       |
| $E_M(V_V)$         | 3.53-4.81        | 2.4*     |
| $E_M(V_{VO})$      | 3.39-4.07        |          |
| $E_M(V_{VO_2})$    | 3.76-4.51        | --       |
| $E_M(V_{V_2})$     | 1.69-2.61        | --       |
| $E_M(V_{V_2O})$    | 2.17-2.92        | --       |
| $E_M(Xe_{V_2})$    | 3.77             | --       |
| $E_M(Xe_{V_2O})$   | 5.28             | --       |
| $E_M(Xe_{V_2O_2})$ | 5.13             | --       |

<sup>1</sup> HJ. Matzke, in Diffusion Processes in Nuclear Materials, ed. R. P. Agarwala, North-Holland, Amsterdam, 1992.

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\* Incorrect assignment.



# Improved Modeling of U and Xe Diffusion

Collaboration with  
CEA Cadarache:

First-principles calculations of uranium diffusion in uranium dioxide

Boris Dorado,<sup>1,2</sup> David A. Andersson,<sup>1,\*</sup> Christopher R. Stanek,<sup>1</sup> Marjorie Bertolus,<sup>2</sup>  
Blas P. Uberuaga,<sup>1</sup> Guillaume Martin,<sup>2</sup> Michel Freyss,<sup>2</sup> and Philippe Garcia<sup>2</sup>

<sup>1</sup>Materials Science and Technology Division, Los Alamos National Laboratory, Los Alamos, New Mexico 87545, USA

<sup>2</sup>CEA, DEN, DEC, Centre de Cadarache, 13108 Saint-Paul-lez-Durance, France

- Previous model assumed that experiments were performed at fixed stoichiometry ( $\text{UO}_{2\pm x}$ ). Incorrect assumption.
- First-principles DFT calculations combined with new thermodynamic model for defect chemistry were used to assess U self-diffusion in nearly stoichiometric  $\text{UO}_2$ .

Updated thermochemical model and  $E_m^{\text{VU,C}}$

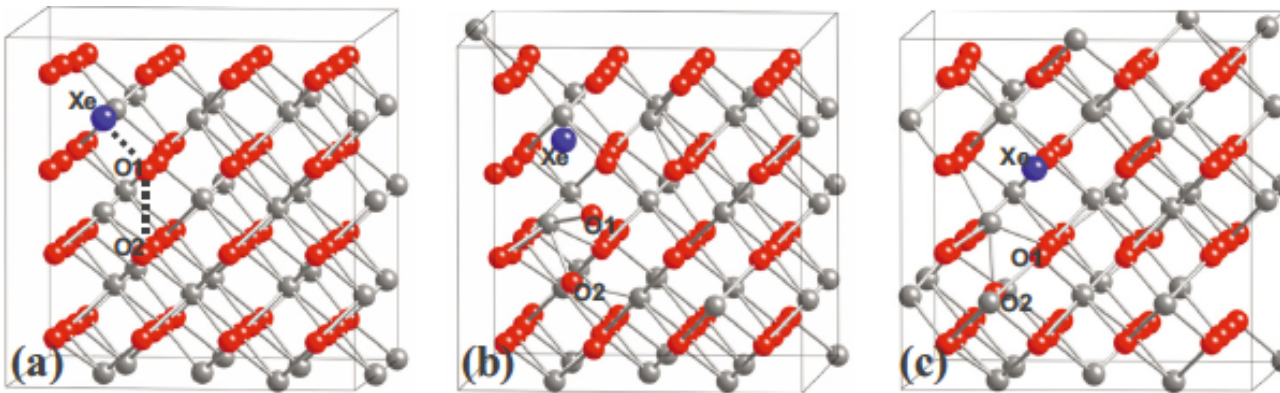
|   | Calc. | Exp[1]  |
|---|-------|---------|
| $\Delta E_a^{\text{U}}(\text{UO}_{2-x})$  | 7.64  | 7.8     |
| $\Delta E_a^{\text{U}}(\text{UO}_2)$      | 3.97  | 5.6/4.4 |
| $\Delta E_a^{\text{U}}(\text{UO}_{2+x})$  | 3.19  | 2.6     |
| $\Delta E_a^{\text{Xe}}(\text{UO}_{2-x})$ | 5.61  | 6.0     |
| $\Delta E_a^{\text{Xe}}(\text{UO}_2)$     | 3.94  | 3.9     |
| $\Delta E_a^{\text{Xe}}(\text{UO}_{2+x})$ | 1.79  | 1.7     |

$$E_a^{\text{VU}} = 2E_{\text{O}_I} + E_S - 2E_{eh} - 2E_{\text{FP}_\text{O}} + E_{\text{pO}_2} + E_m^{\text{VU}}$$

- Most favorable mechanism: O-assisted vacancy mechanism with activation energy 4.1-4.9 eV (experimental value: 4.4 eV).
- Interstitial diffusion gives higher  $E_a$ . The U interstitial(cy) migration barrier is 3.7 eV.

## Interstitial Xe Diffusion in $\text{UO}_2$

Interstitial diffusion mechanism relevant if thermal or radiation-induced defects (i.e. vacancies) are present only in low concentrations.



|                              |           |
|------------------------------|-----------|
| $E_M(\text{Xe}_i) \text{ A}$ | 4.48–5.29 |
| $E_M(\text{Xe}_i) \text{ B}$ | 1.6-2.41  |

Liu et al (*APL*, **98** (2011) 151902)

$\Delta Q$  from fuel performance models:

|                | $\Delta Q$ [eV] |                | $\Delta Q$ [eV] |
|----------------|-----------------|----------------|-----------------|
| Q1 F&M [2007]  | 3.09            | Q2 F&M Frapcon | 1.97            |
| Q2 F&M [2007]  | 1.19            | Q3 F&M Frapcon | 0.82            |
| Q1 F&M Frapcon | 0.57            | ANS5.4         | 3.14            |

# First Principles Analysis of Intermediate T Mechanisms

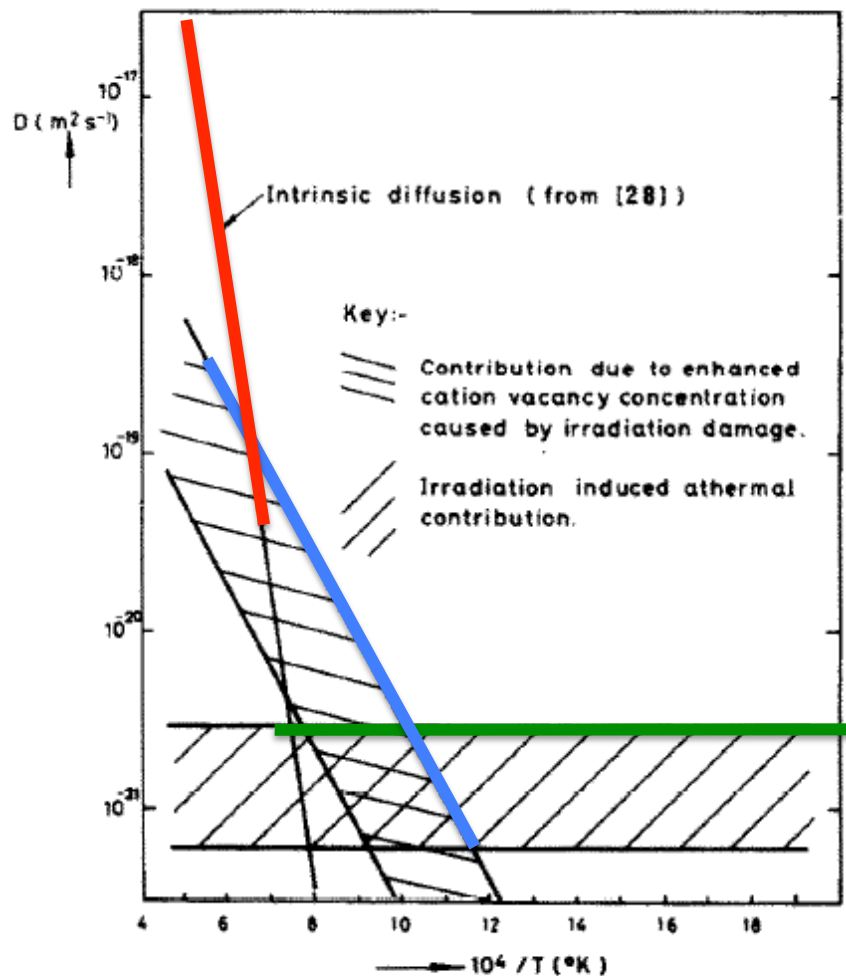


Fig. 10. Possible component coefficient.

Further analysis required, alternative mechanisms may be important for intermediate T and high T.

Traditionally explained by enhanced vacancy concentration according to:

$$D_2 = s^2 J_V V \quad V \approx V_{irr} = \sqrt{K' / J_V Z}$$

$$D_2 = \text{constant} \times \sqrt{\dot{F}} \exp\left(\frac{-1.2}{k_B T}\right)$$

Obtained by assuming:  $J_V \propto \exp\left(-\frac{2.4}{k_B T}\right)$

$$J_{Xe} \propto \exp\left(-\frac{E_m^{Xe_{U_2O}} - E_B^{Xe_{U_2O}}}{k_B T}\right)$$

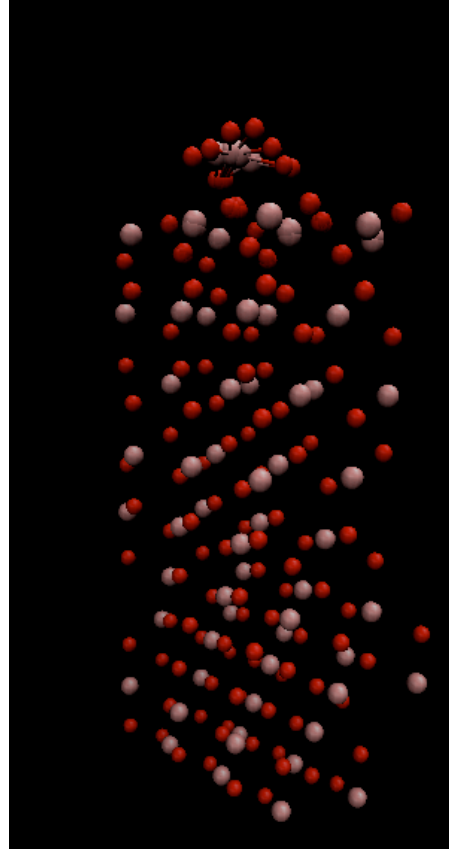
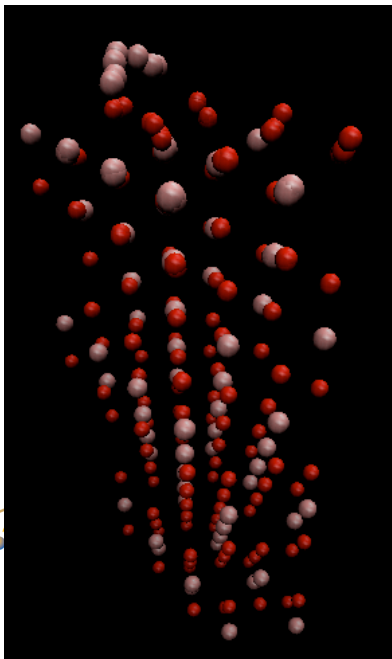
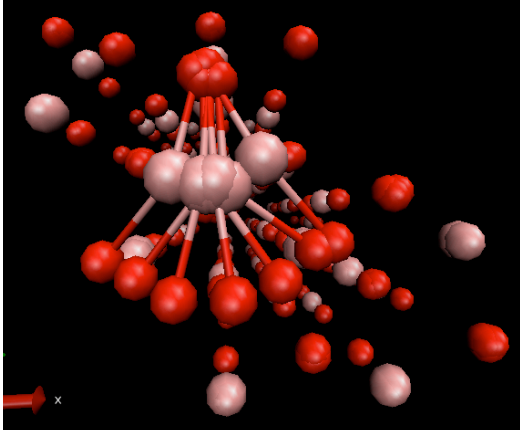
From DFT:

$$J_V \propto \exp\left(-\frac{E_m^{V_{U_2}}}{k_B T}\right)$$

Applying the same assumption as above yields 3.17 eV. Interestingly this is close to the high temperature regime.



# Bubble Migration Controlled by Surface Diffusion



- Difficult to study extended Xe clusters due to size effects.
- Investigate limiting case represented by a (111) surfaces.
- $\text{UO}_2$  species have a barrier of 1.01 eV on (111) surfaces.
- U atoms have a barrier of 1.26 eV on (111) surfaces.
- Sub-surface U vacancies have a barrier that is about 1 eV lower than bulk barriers.
- Simplified model, rate limiting step for bubble diffusion?  
Contribution to intermediate T gas release?

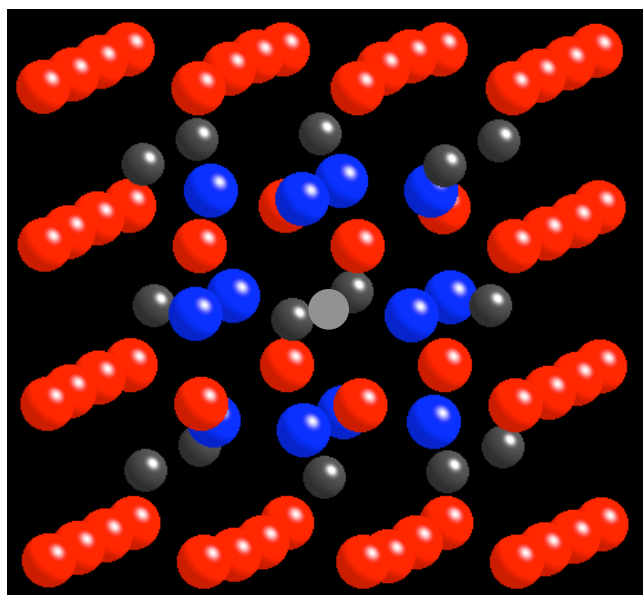
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## $\text{UO}_{2+x}$ and $\text{U}_4\text{O}_9$ structure models

Bevan *et al.*<sup>1</sup> proposed the so-called cubo-octahedron cluster for  $\text{UO}_{2+x}$  and  $\text{U}_4\text{O}_{9-y}$ .

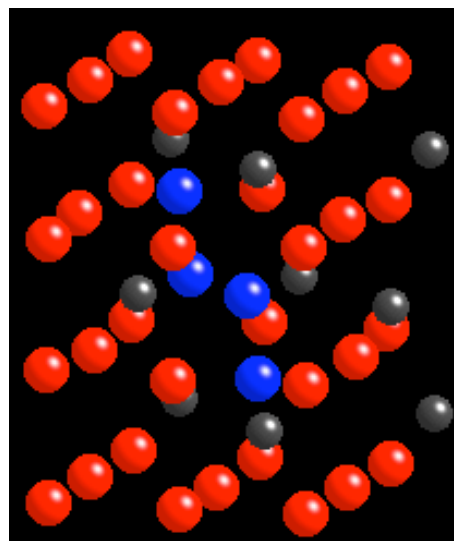
### Cubo-octahedron



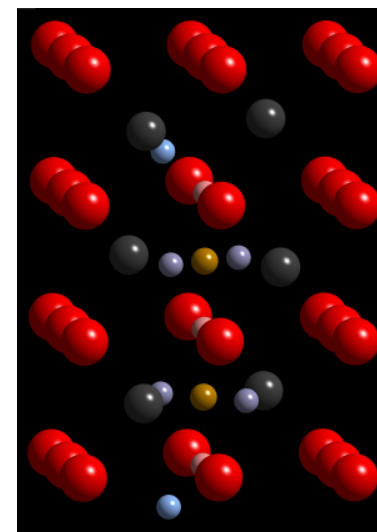
The point defect character in  $\text{UO}_{2+x}$  was shown to be a function of T and x.

Willis *et al.*<sup>1</sup> found clustering of interstitial-like oxygen ions; introduced to types of interstitial ions, O' and O'', to explain neutron diffraction data.

### Willis 2:2:2



### Willis 4:3:2

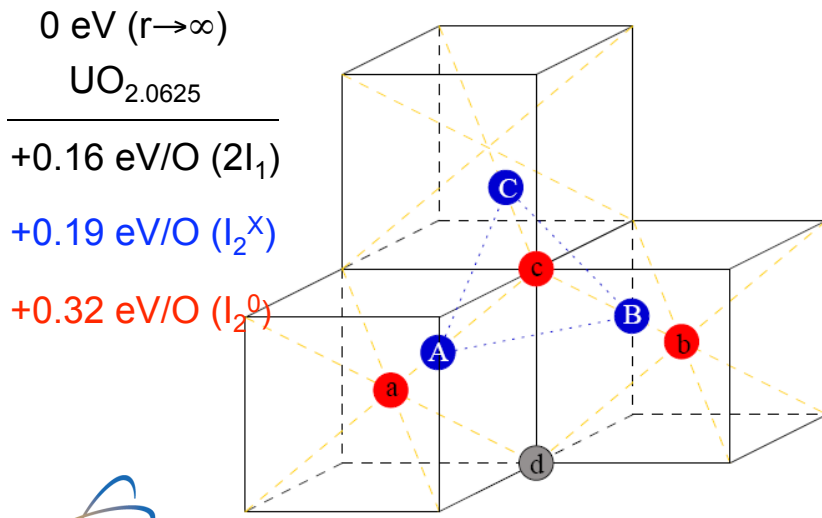


Failed to build  $\text{U}_4\text{O}_9$  structure model based on the Willis 2:2:2 cluster.

# Di-interstitial and quad-interstitial clusters in $\text{UO}_{2+x}$ from DFT

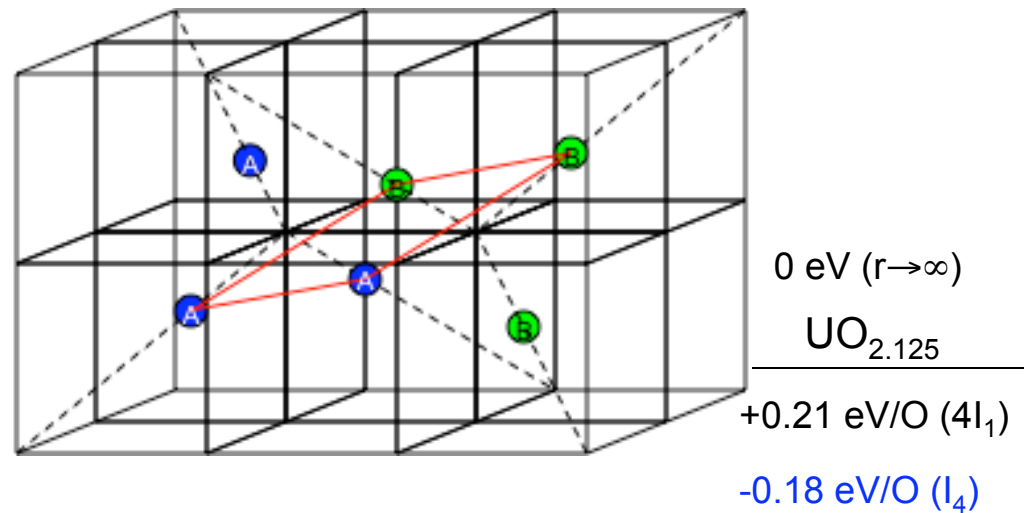
- $\text{I}_2^x$  is the most stable configuration of di-interstitials, less stable than  $\text{I}_1$ .
- $\text{I}_4^x$  is the most stable state of excess oxygen ions in  $\text{UO}_{2+x}$
- Although related, details differ from Willis and cuboctahedral clusters found from neutron diffraction.

## Split di-interstitial ( $\text{I}_2^x$ )



The split di-interstitial (blue) is formed from two NN octahedral interstitials that dislocate a regular oxygen ion (red).

## Split quad-interstitial ( $\text{I}_4^x$ )

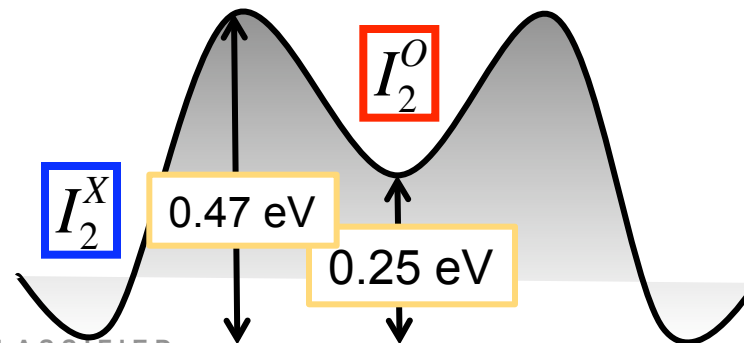
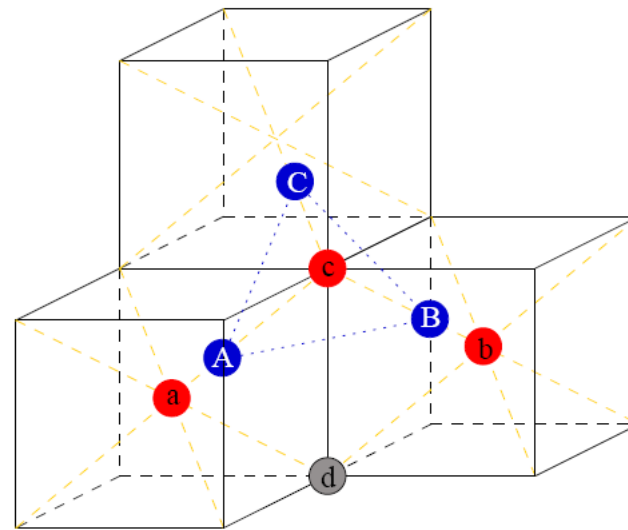


Two split di-interstitials (blue and green) make up a stable cluster in  $\text{AnO}_{2+x}$ .

## Diffusion of Split Di-interstitials

- Split di-interstitial ( $I_2^X$ ) can diffuse via intermediate state which is octahedral  $I_2$  structure ( $I_2^O$ )
- Migration barrier is 0.47 eV, compared to 0.81 eV for mono-interstitials (interstitialcy mechanism).

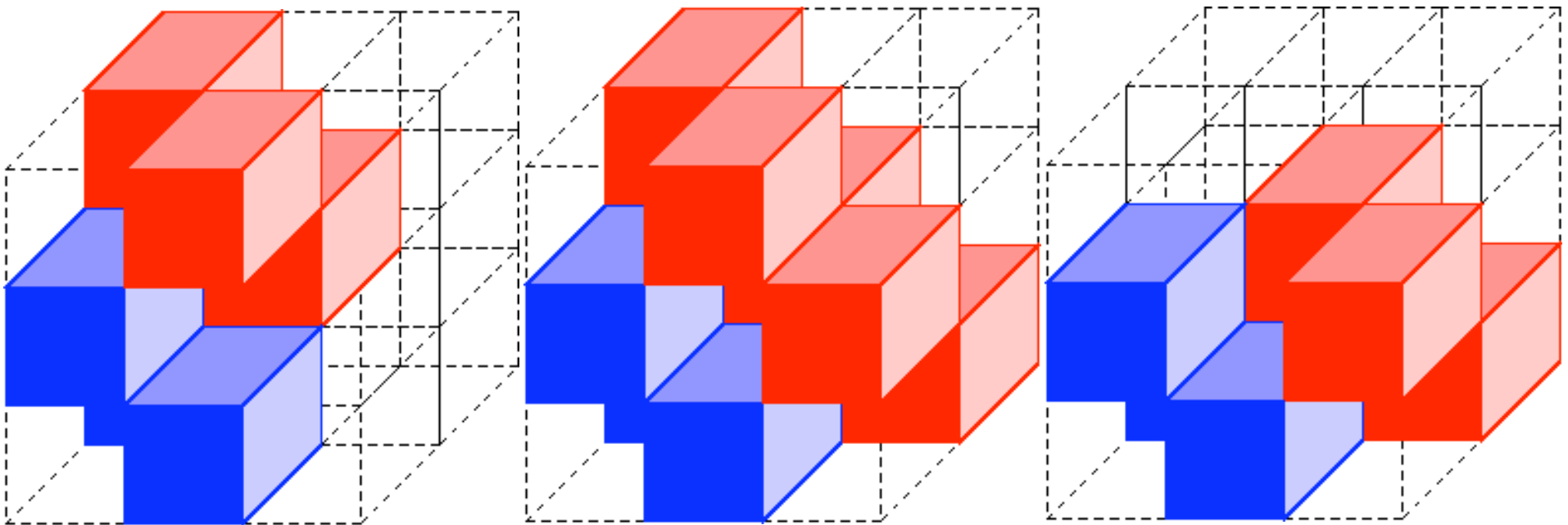
Collaboration with C. Deo et al., Georgia Tech.



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## Diffusion of Split Quad-Interstitials

- Split quad-interstitial ( $I_4^X$ ) can diffuse via one component  $I_2^X$  “rotating” to new position
- Migration barrier is 0.97 eV, compared to 0.81 eV for mono-interstitials.



# kMC Models for Oxygen Self-Diffusion

**Taku Watanabe, Rakesh Behera and Chaitanya Deo**

*Georgia Institute of Technology*

## ■ **Model 1: mono-interstitials only (Murch model)**

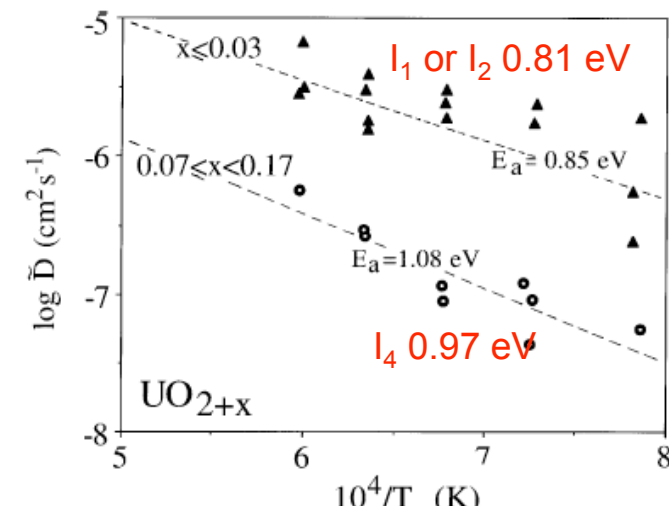
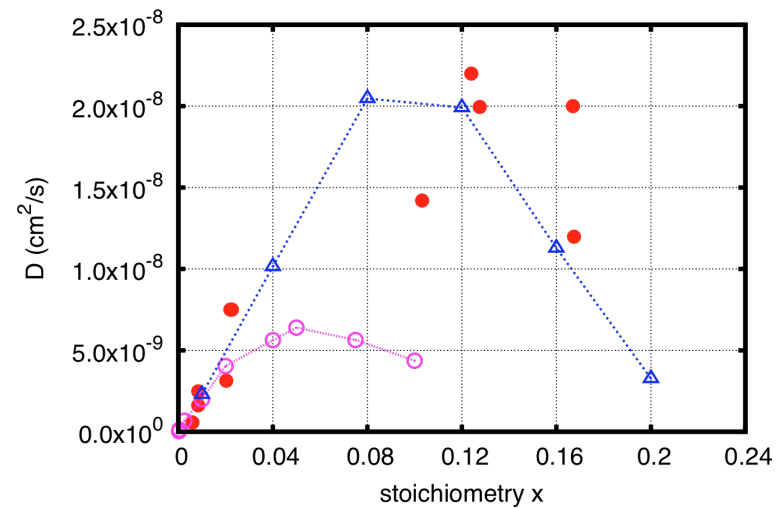
- $I_1$  diffuse with barrier of 0.81 eV
- $I_1$  block all nearest neighbor sites

## ■ **Model 2: mono- plus di-interstitials**

- Philosophy: as simple an extension of Murch as possible
- $I_1$  diffuse with barrier of 0.81 eV
- $I_2$  form when 2  $I_1$  become neighbors
- $I_1$  can be neighbors of at most one other  $I_1$  (forming  $I_2$ )
  - If an  $I_1$  tries to jump to a site where it would neighbor more than one other  $I_1$ , that move is unallowed
- $I_2$  diffuse with barrier of 0.47 eV
  - $I_2$  cannot be nearest neighbor of any other species (like Murch blocking)
- $I_2$  are higher in energy than 2\* $I_1$  by 0.38 eV (from LDA+U)
- Breakup barrier of  $I_2$  would be 0.43 eV (0.81-0.38)
  - Position of new  $I_1$  would depend on available sites

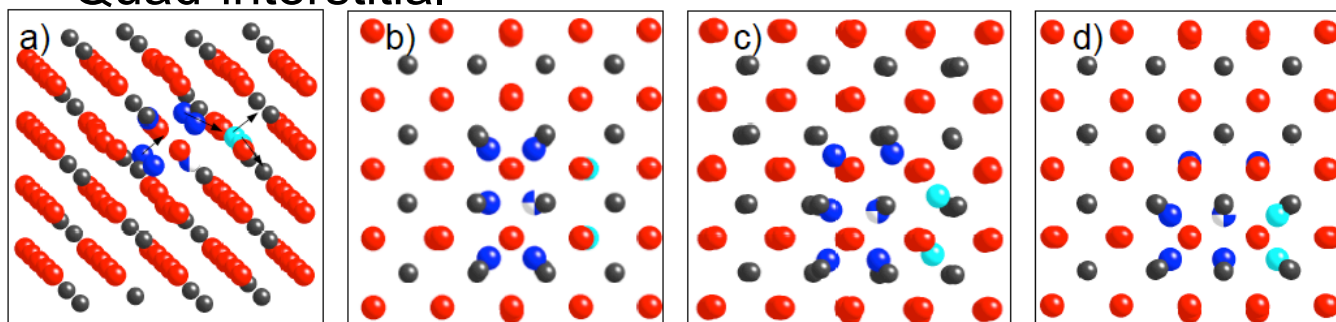
# Diffusion: Theory vs Experiment

- KMC simulation of oxygen self-diffusion in  $\text{UO}_{2+x}$  at 1073 K
- Results agree well at low  $x$ 
  - Likely describing mono-interstitial diffusion well
- At larger  $x$ ,  $I_1$  model quickly falls off, in disagreement with experiment
- By including the split di-interstitial mechanism, we are able to better reproduce the experimental data.
  - Mainly due to different different blocking
- Larger clusters for high  $x$ ?  $I_1$  or  $I_2$  vs.  $I_4$  barriers agree with conductivity experiments.

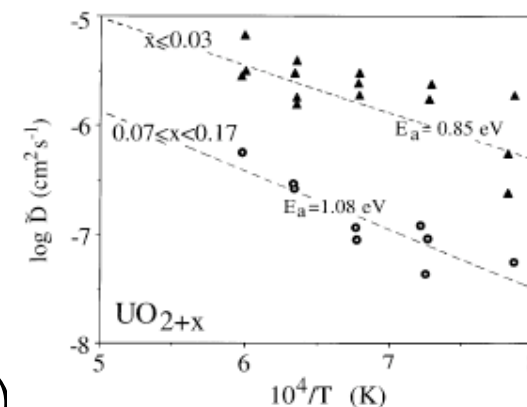


# Improved Description of Cluster Diffusion in $\text{UO}_{2+x}$

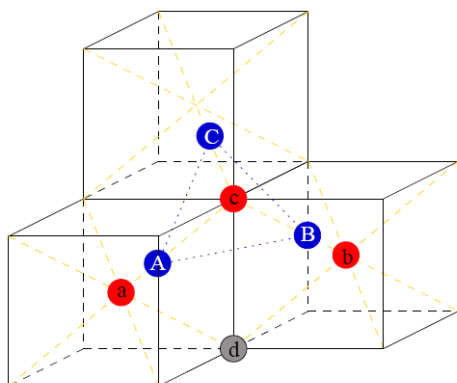
Quad-interstitial



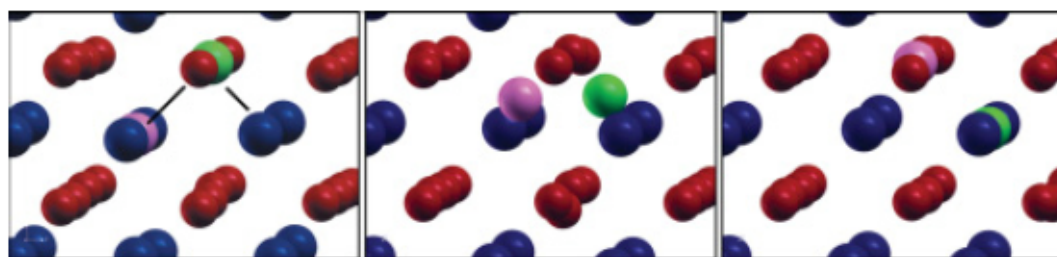
Ruello et al.



Di-interstitial



Mono-interstitial (from Dorado et al.)



- Exp. barriers:  $I_1$ : ~1.3 eV,  $I_2$ : 0.85 eV,  $I_4$ : 1.08 eV
- Calculated barriers:  $I_1$ : 1.31 eV,  $I_2$ : 0.87 eV,  $I_4$ : 1.13 eV
- Implement in kMC for upscaling to continuum.

## Conclusions

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- DFT to establish that bulk Xe diffusion in  $\text{UO}_{2+x}$  occurs by binding a second  $V_U$  to the Xe trap site clusters.
- Accurate activation energies for Xe and U transport from DFT when charge compensation, clustering and thermo-chemistry is accounted for.
- Initial analysis of gas release models with respect to DFT database indicate possible discrepancies for in particular the intermediate temperature regime.
- U (111) surface diffusion was investigated as a model system for diffusion of small fission gas bubbles. An activation energy of 1.0-1.2 eV was predicted for the rate limiting step.
- Oxygen transport as function of stoichiometry (x in  $\text{UO}_{2+x}$ ) studied with a combination of DFT and kMC. Good agreement with experimental measurements when formation of di-interstitial and quad-interstitial clusters are accounted for.